



Market News

Infineon launches the sixth generation of CoolSiC™ Schottky diodes 650 V for fast switching

Munich, Germany – 26 September 2017 – Infineon Technologies AG (FSE: IFX / OTCQX: IFNNY) introduces the CoolSiC™ Schottky diode 650 V G6. This latest development in the CoolSiC diode family is built upon the distinctive characteristics of the G5, providing reliability, quality, and increased efficiency. The CoolSiC G6 diodes are a perfect complement to the 600 V and 650 V CoolMOS™ 7 families. They are aiming at current and future applications in [Server](#) and [PC power](#), [Telecom equipment power](#), and [PV inverters](#).

The CoolSiC Schottky diode 650 V G6 has a new layout, new cell structure, and a new proprietary Schottky metal system. The result is an industry benchmark V_F (1.25 V), and a $Q_c \times V_F$ figure of merit (FOM) which is 17 percent lower than the previous generation. In addition, the new G6 diode makes use of the SiC strong characteristics of temperature independent switching behavior and no reverse recovery charge.

The design of the device provides improved efficiency over all load conditions along with increased system power density. Thus, the CoolSiC Schottky diode 650 V G6 features reduced cooling requirements, increased system reliability, and extremely fast switching. The new device is the SiC diode generation with the best price performance.

Availability

The CoolSiC Schottky diode 650 V G6 is available now. More information is available at www.infineon.com/cool-sic-g6.

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